



### **DUAL P-CHANNEL ENHANCEMENT MODE MOSFET**

## **Product Summary**

BV <sub>DSS</sub>	Rds(on) max	ID MAX @T <sub>A</sub> = +25°C
-20V	0.75Ω @ V <sub>GS</sub> = -4.5V	-0.63A
-20V	1.05Ω @ V <sub>GS</sub> = -2.5V	-0.54A

### **Description**

This new generation MOSFET is designed to minimize the on-state resistance (RDS(ON)) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## **Applications**

- Battery Operated Systems and Solid-State Relays
- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc.
- Power Supply Converter Circuits

### **Features and Benefits**

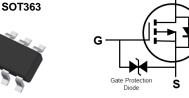
- Low On-Resistance
- Low Gate Threshold Voltage
  - Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Complementary Pair MOSFET
- Ultra-Small Surface Mount Package
- **ESD Protected**
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

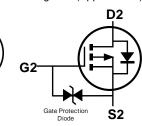
#### **Mechanical Data**

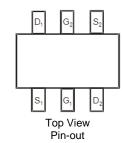
- Case: SOT363
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish Annealed over Alloy 42 Leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208@3
- Terminal Connections: See Diagram
- Weight: 0.006 grams (Approximate)











Top View

Q1 P-CHANNEL

Q2 P-CHANNEL

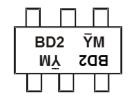
## Ordering Information (Note 4)

Part Number	Case	Packaging
DMP2900UDW-7	SOT363	3,000/Tape & Reel
DMP2900UDW-13	SOT363	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

# Marking Information



BD2 = Product Type Marking Code YM = Date Code Marking  $\overline{Y}$  = Year (ex: I = 2021) M = Month (ex: 9 = September)

Date Code Key

Year	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031
Code	Н	I	J	K	L	М	Ν	0	Р	R	S	T
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec

DMP2900UDW Document number: DS42960 Rev. 3 - 2



### **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteris	Symbol	Value	Unit
Drain-Source Voltage	VDSS	-20	V
Gate-Source Voltage	Vgss	±6	V
Continuous Drain Current (Note 6) V <sub>GS</sub> = -4.5V	lo	-0.63 -0.5	А
Maximum Continuous Body Diode Forward Current	Is	-0.42	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%	Ірм	-2.5	А

# Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T <sub>A</sub> = +25°C	PD	0.37	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R <sub>θ</sub> JA	340	°C/W
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	PD	0.46	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	RθJA	272	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

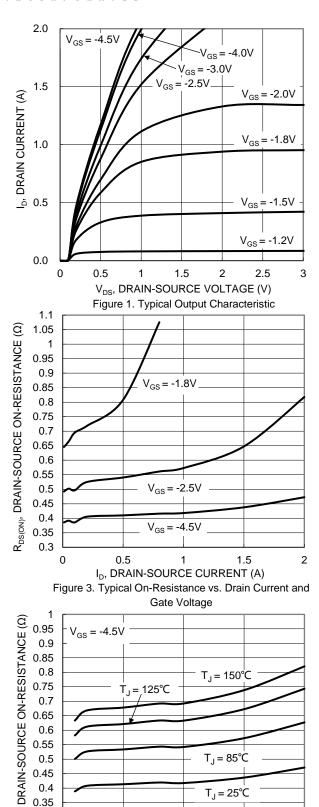
# Electrical Characteristics (T<sub>A</sub> = +25°C, V<sub>BIAS</sub> = 5V, V<sub>IN</sub> = 1.05V, unless otherwise specified.)

Characteristic		Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage		BV <sub>DSS</sub>	-20	_	_	V	$V_{GS} = 0V, I_{D} = -250\mu A$
Zero Gate Voltage Drain Current	ero Gate Voltage Drain Current @T <sub>C</sub> = +25°C		_	_	-100	nA	V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V
Gate-Source Leakage	Igss	_	_	±2.0	μΑ	VGS = ±4.5V, VDS = 0V	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage		VGS(TH)	-0.5	_	-1.0	٧	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA
				0.4	0.75		V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -430mA
Static Drain-Source On-Resistance		RDS(ON)	_	0.53	1.05	Ω	V <sub>GS</sub> = -2.5V, I <sub>D</sub> = -300mA
				0.7	1.5		$V_{GS} = -1.8V, I_D = -150mA$
Diode Forward Voltage (Note 7)		V <sub>SD</sub>	_	-0.7	-1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -150mA
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance		Ciss	_	49	_	pF	
Output Capacitance		Coss	_	12	_	pF	V <sub>DS</sub> = -16V, V <sub>GS</sub> = 0V, f = 1.0MHz
Reverse Transfer Capacitance		Crss	_	3.4	_	pF	1 = 1.0IVII 12
Total Gate Charge		Qg	_	0.7	_	nC	
Gate-Source Charge		Qgs	_	0.1	_	nC	$V_{GS} = -4.5V$ , $V_{DS} = -10V$ , $I_{D} = -250$ mA
Gate-Drain Charge		Q <sub>gd</sub>	_	0.1	_	nC	ID = -250IIIA
Turn-On Delay Time		t <sub>D(ON)</sub>	_	16	_	ns	101/1/
Turn-On Rise Time	·		_	15	_	ns	V <sub>DS</sub> = -10V, V <sub>GS</sub> = -4.5V,
Turn-Off Delay Time		tD(OFF)	_	213	_	ns	$R_g = 10\Omega, R_L = 47\Omega$ $I_D = -200 \text{mA}$
Turn-Off Fall Time	·	tF	_	89	_	ns	ID = -200IIIA
Reverse Recovery Time		trr	_	10.5	_	ns	In - 1 A di/dt - 100 A/ug
Reverse Recovery Charge		Q <sub>RR</sub>	_	1.8	_	nC	I <sub>F</sub> = 1A, di/dt = 100A/μs

5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

S. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to production testing.





I<sub>D</sub>, DRAIN CURRENT (A) Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

1

 $T_J = 85^{\circ}C$ 

 $T_J = 25^{\circ}C$ 

 $T_J = -55^{\circ}C$ 

1.5

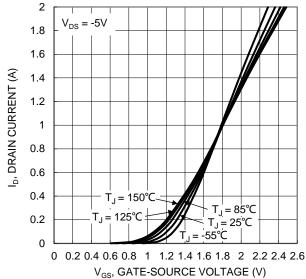
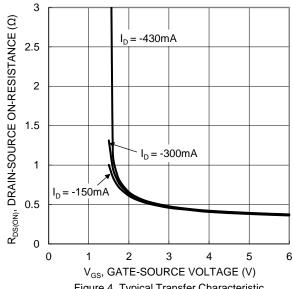


Figure 2. Typical Transfer Characteristic



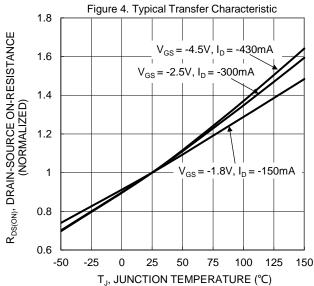


Figure 6. On-Resistance Variation with Junction Temperature

0.5

0.55

0.5

0.45 0.4

0.35

0.3 0.25

0.2

0

2



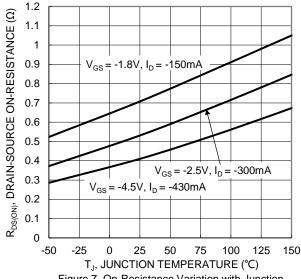
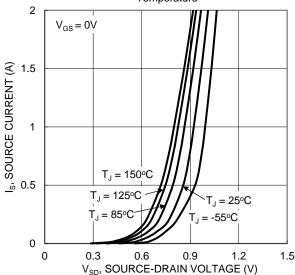
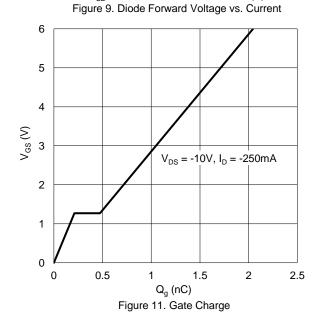


Figure 7. On-Resistance Variation with Junction Temperature





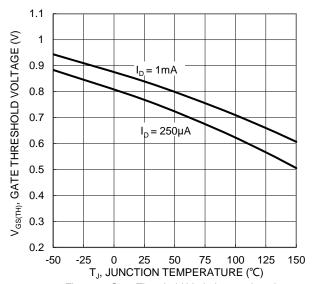
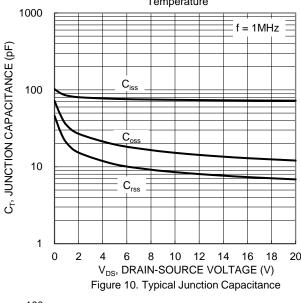
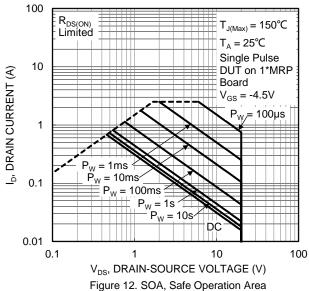


Figure 8. Gate Threshold Variation vs. Junction Temperature







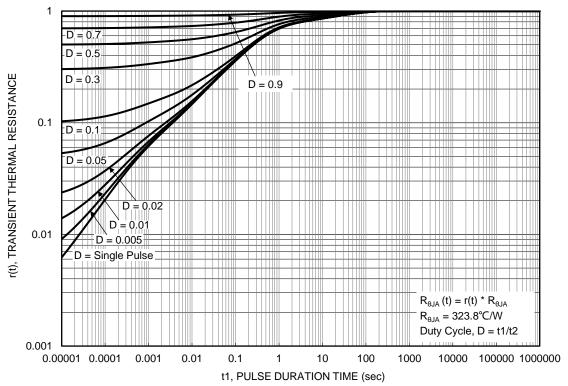


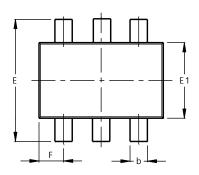
Figure 13. Transient Thermal Resistance

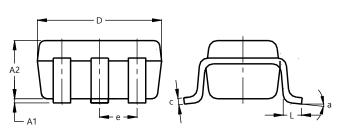


## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### **SOT363**



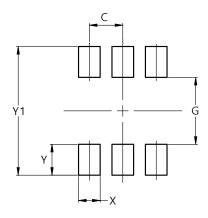


SOT363						
Dim	Min	Max	Тур			
A1	0.00	0.10	0.05			
A2	0.90	1.00	0.95			
b	0.10	0.30	0.25			
C	0.10	0.22	0.11			
D	1.80	2.20	2.15			
Е	2.00	2.20	2.10			
E1	1.15	1.35	1.30			
e	C	.650 E	SC			
F	0.40	0.45	0.425			
L	0.25	0.40	0.30			
а	0°	8°				
All Dimensions in mm						

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### **SOT363**



Dimensions	Value (in mm)
С	0.650
G	1.300
Х	0.420
Υ	0.600
Y1	2.500



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